

## BR103

SILICON PLANAR THYRISTOR

High-reliability discrete products and engineering services since 1977

#### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS					
Rating	Symbol	Value	Unit		
Negative and positive repetitive peak off state voltage	V <sub>RR</sub> /V <sub>DR</sub>	30	V		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	0.8	А		
Surge on state current, sinusoidal pulse (t <sub>p</sub> < 10ms)	I <sub>TSM</sub>	6	А		
Repetitive surge on-state current at $t_p$ = 6µs and f = 40kHz sine	Ι <sub>τ</sub>	2	А		
Peak gate forward current	I <sub>GFP</sub>	0.5	А		
Repetitive reverse gate voltage	V <sub>(KG)R</sub>	6	V		
Storage and junction temperature range	T <sub>stg</sub> , TJ	-40 to +125	°C		
Average gate power dissipation	P <sub>G(AV)</sub>	0.01	W		
Peak gate power dissipation	P <sub>GP</sub>	0.1	W		

#### **ELECTRICAL CHARACTERISTICS (**T<sub>c</sub> = 25°C)

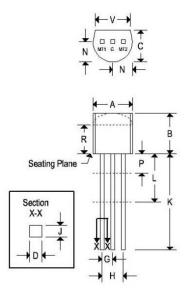
Characteristic	Symbol	Value	Unit		
STATIC CHARACTERISTICS					
Continuous reverse blocking and off state current $(R_{GK}=1k\Omega) \label{eq:GK} (T_{J}=125^{\circ}C)$	I <sub>R</sub> /I <sub>D</sub>	<2 <50	μΑ		
Holding current $(R_{GK} = 1k\Omega)$ $(T_{J} = -40^{\circ}C)$	I <sub>H</sub>	<3 <4	mA		
On-state voltage (I <sub>TS</sub> = 1A, t <sub>p</sub> = 1ms)	V <sub>T</sub>	<1.5	V		
Gate trigger current ( $V_{AK} = 6V, R_L = 100\Omega$ ) ( $T_J = 0^{\circ}C$ )	I <sub>GT</sub>	<200 <250	μА		
Gate trigger voltage $(V_{AK}=6V,R_L=100\Omega,R_{GT}=1k\Omega,T_J=0^\circ\text{C})$	V <sub>GT</sub>	<0.9	v		
Gate non-trigger forward voltage $(V_D = V_{DR}, R_{GK} = 1k\Omega, T_J = 125^{\circ}C)$	V <sub>GF</sub>	>0.1	V		
Critical rate of voltage rise $(R_{GK} = 1k\Omega, T_J = 125^{\circ}C, V_{AK} = 10V)$	dv/dt	10	V/µs		
Turn-off time ( $I_{TS(rectangular)} = 1A, t_p = 50 \mu s$ )	tq	<6	μs		
Turn-on time ( $V_D = V_{DR}$ , $R_L = 100\Omega$ , $R_{GK} = 1k\Omega$ , $I_{GTS} = 1.4mA$ , $t_p = 5\mu s$ , $t_r = 40ns$ )	t <sub>on</sub>	1.2	μs		



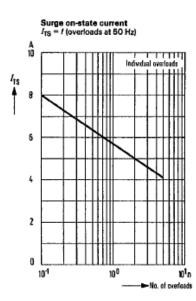
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#### MECHANICAL CHARACTERISTICS

Case	TO-92
Marking Body painted, alpha-numeric	
Pin out	See below



	TO-92				
	Inches		Millimeters		
	Min	Max	Min	Max	
Α	0.175	0.205	4.450	5.200	
В	0.170	0.210	4.320	5.330	
С	0.125	0.165	3.180	4.190	
D	0.016	0.022	0.410	0.550	
F	0.016	0.019	0.410	0.480	
G	0.045	0.055	1.150	1.390	
Н	0.095	0.105	2.420	2.660	
J	0.015	0.020	0.390	0.500	
K	0.500		12.700		
L	0.250	1	6.350	-	
Ν	0.080	0.105	2.040	2.660	
Р	-	0.100	-	2.540	
R	0.115	-	2.930	-	
٧	0.135	-	3.430	-	

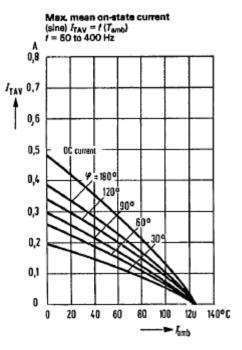


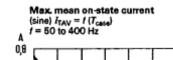
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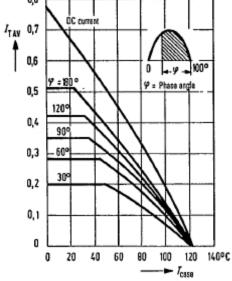
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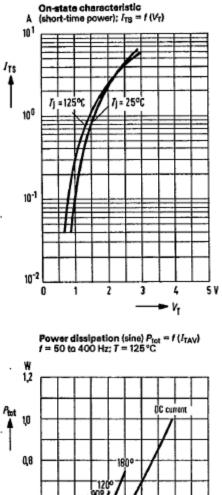


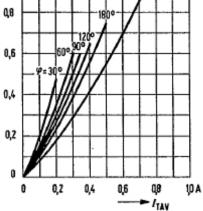


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Rev. 20130118



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## **BR103**

### SILICON PLANAR THYRISTOR

60 80 100 AVERAGE FORWARD CUR

AVERAGE FORWARD CURRENT

JUNCTION TE

3 4 5 PULSE WIDTH-MILLISECONDS

1.5

20 140 - AMPERES

160

120

